

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-4 (Canceled)

Claim 5 (Currently Amended)): The semiconductor device according to Claim [[2]]
16, wherein

said first, fourth, second and third semiconductor layers are adjacent to each other in
this order, and

said first and second semiconductor layers function as source/drain layers of MOS
transistors having conductivity types different from each other, respectively.

Claim 6 (Currently Amended): The semiconductor device according to Claim [[2]]
16, further comprising a cover having an insulative surface in contact with said portion of
said pn junction separated from said isolator.

Claim 7 (Original): The semiconductor device according to Claim 5, further
comprising

a cover having a insulative surface in contact with said portion of said pn junction
separated from said isolator.

Claim 8 (Currently Amended): The semiconductor device according to claim [[2]]
16, wherein

said second semiconductor layer is provided in said fourth semiconductor layer, said first semiconductor layer includes a pair of first semiconductor layers being formed in said second semiconductor layer, and

said pair of first semiconductor layers function as a contact with respect to said second semiconductor layer.

Claim 9 (Original): A semiconductor device comprising:

a substrate at least having an insulative surface;

a semiconductor film provided on said surface of said substrate, having at least one pn junction extending in a thickness direction of said substrate, said at least one pn junction including a pn junction which is applied with voltage; and

a metallic compound layer selectively formed on said semiconductor film, being a compound of said semiconductor film and metal, wherein

a maximum value of a distance between at least said pn junction which is applied with voltage and a boundary between said metallic compound layer and said semiconductor film is not more than $2\mu\text{m}$, when a direction from said boundary to said semiconductor film along said surface of said substrate is taken as a positive direction.

Claim 10 (Original): The semiconductor device according to Claim 9, further comprising a mask provided on said at least one pn junction for preventing silicidation with metal of said semiconductor film.

Claim 11 (Currently Amended): The semiconductor device according to Claim ~~11~~ 10, wherein said mask has the same structure as a gate of a MOS transistor to be formed on said semiconductor film in a thickness direction thereof.

Claim 12 (Original): A resistor comprising:
a substrate at least having an insulative surface;
a first semiconductor layer of a first conductivity type provided on said surface of said substrate;
an insulative insulator formed on a surface of said first semiconductor film on the far side from said substrate, separately from said surface of said substrate; and
a second semiconductor layer of a second conductivity type opposite to said first conductivity type formed in said first semiconductor layer, said second semiconductor layer forming a pn junction in conjunction with said first semiconductor layer, said pn junction extending from said surface of said first semiconductor layer to said surface of said substrate and being separated from said insulator.

Claim 13 (Original): The resistor according to Claim 12, further comprising
a pair of third semiconductor layers of said second conductivity type formed in said second semiconductor layer, having an impurity concentration higher than that of said second semiconductor layer.

Claim 14 (Original): The resistor according to Claim 13, further comprising
a gate electrode covering said pn junction.

Claim 15 (Original): The resistor according to Claim 13, further comprising
a cover having an insulative surface in contact with said portion of said pn junction
separated from said isolator.

Claim 16 (New) A semiconductor device comprising: u
a substrate at least having an insulative surface;
a semiconductor film provided on said surface of said substrate comprising a first
semiconductor layer of a first conductivity type, a second semiconductor layer of said first
conductivity type having an impurity concentration lower than that of said first
semiconductor layer, a third semiconductor layer of a second conductivity type opposite to
said first conductivity type and a fourth semiconductor layer of said second conductivity type
having an impurity concentration lower than that of said third semiconductor layer; and
an insulative isolator formed on a surface of said semiconductor film on the far side
from said substrate, separately from said surface of said substrate, wherein
said second and fourth semiconductor layers form a pn junction extending in the
thickness direction of said semiconductor film, said pn junction has a portion separated from
said isolator
a maximum value of a distance between said pn junction and a boundary between said
isolator and said semiconductor film is not more than $2\mu\text{m}$, when a direction from said
boundary to said isolator along said surface of said substrate is taken as a positive direction.